CLAIMS

1. A sputtering target for a magnetic recording medium, comprising:

a metal phase and an oxide phase,

wherein the metal phase contains, based on total metal phase components of the sputtering target for a magnetic recording medium, 1 mol% or more and 30 mol% or less of Pt and 0.5 mol% or more and 10 mol% or less of at least one or more selected from Mn and V, with the balance being Co and incidental impurities; and

wherein the oxide phase contains O and at least one element selected from a group consisting of B, V, Ru, Ti, Si, Ta, Cr, Nb, Mn, Co, Ni, Zn, Y, Mo, W, La, Ce, Nd, Sm, Eu, Gd, Yb, Lu, and Zr,

wherein the oxide phase contains at least B, and wherein the sputtering target contains, based on the sputtering target for a magnetic recording medium as a whole, 25 vol% or more and 40 vol% or less of the oxide phase.

2. A sputtering target for a magnetic recording medium, comprising:

a metal phase and an oxide phase,

wherein the metal phase contains, based on total metal phase components of the sputtering target for a magnetic recording medium, 1 mol% or more and 30 mol% or less of Pt, 0.5 mol% or more and 10 mol% or less of at least one or more selected from Mn and V, and more than 0.5 mol% and 30 mol% or less of Ru, with the balance being Co and incidental impurities; and

wherein the oxide phase contains O and at least one element selected from a group consisting of B, V, Ru, Ti, Si, Ta, Cr, Nb, Mn, Co, Ni, Zn, Y, Mo, W, La, Ce, Nd, Sm, Eu, Gd, Yb, Lu, and Zr,

wherein the oxide phase contains at least B, and

wherein the sputtering target contains, based on the sputtering target for a magnetic recording medium as a whole, 25 vol% or more and 40 vol% or less of the oxide phase.

3. A sputtering target for a magnetic recording medium, comprising:

a metal phase and an oxide phase,

wherein the metal phase contains, based on total metal phase components of the sputtering target for a magnetic recording medium, 1 mol% or more and 30 mol% or less of Pt and 0.5 mol% or more and 10 mol% or less of at least one or more selected from Mn and V, with the balance being Co and incidental impurities; and

wherein the oxide phase contains an oxide of at least one element selected from B, V, Ru, Ti, Si, Ta, Cr, Nb, Mn, Co, Ni, Zn, Y, Mo, W, La, Ce, Nd, Sm, Eu, Gd, Yb, Lu, and Zr, and

wherein the sputtering target contains, based on the sputtering target for a magnetic recording medium as a whole, 25 vol% or more and 40 vol% or less of the oxide phase.

4. A sputtering target for a magnetic recording medium, comprising:

a metal phase and an oxide phase,

wherein the metal phase contains, based on total metal phase components of the sputtering target for a magnetic recording medium, 1 mol% or more and 30 mol% or less of Pt, 0.5 mol% or more and 10 mol% or less of at least one or more selected from Mn and V, and more than 0.5 mol% and 30 mol% or less of Ru, with the balance being Co and incidental impurities; and

wherein the oxide phase contains an oxide of at least one element selected from B, V, Ru, Ti, Si, Ta, Cr, Nb, Mn, Co, Ni, Zn, Y, Mo, W, La, Ce, Nd, Sm, Eu, Gd, Yb, Lu, and Zr, and

wherein the sputtering target contains, based on the sputtering target for a magnetic recording medium as a whole, 25 vol% or more and 40 vol% or less of the oxide phase.